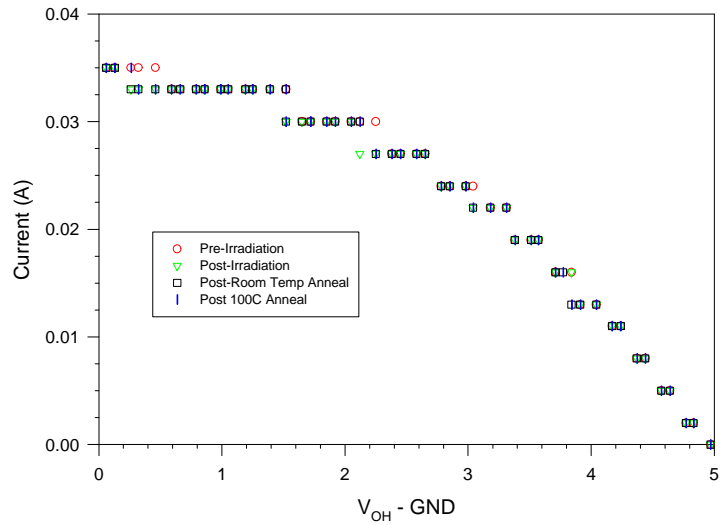


Devices were irradiated to 11 kRads (Si) at 4 kRads (Si) / day. This was followed by a 168 hour room temperature anneal and then a 168 hour 100°C anneal.

A14100A/MEC  
D/C 9819 - UCL055  
LAN109  $V_{OH}$   
NASA/GSFC  
August, 1998



A14100A/MEC  
D/C 9819 - UCL055  
LAN109  $V_{OL}$   
NASA/GSFC  
August, 1998

